



[NAME OF DOCUMENT] Abstract

[ABSTRACT]

[OBJECT] To provide a process capable of forming a good underlying film at the interface between an insulating film and an electronic device substrate so as to improve the resultant transistor characteristic.

[SOLVING MEANS]

The surface of an insulating film disposed on an electronic device substrate is irradiated with plasma based on a process gas comprising at least an oxygen atom-containing gas, to thereby form an underlying film at the interface between the insulating film and the electronic device substrate.

[SELECTED FIGURE] Fig. 16